

Application No. 09/768,912  
Amendment dated: March 22, 2004  
Reply to Final Office Action of February 13, 2004

**IN THE CLAIMS**

1 - 8. (Canceled)

9. (Currently amended) A semiconductor device comprising:

a single-crystal substrate made of a material different from nitride III-V compound semiconductors, and, said substrate extending between a first surface and a second surface opposite said first surface and having a hole extending through the substrate from said first surface to said second surface;

a device formed on one major surface of said first and second surfaces of said single-crystal substrate by using III-V compound semiconductors[.];

a layer disposed on said major surface one of said first and second surfaces of said single-crystal substrate and in electrical connection with said device; and;

wherein said device is formed between said layer and said substrate and is electrically connected to said layer; and

a via hole formed in said single-crystal substrate through to said layer;

wherein an electrical connection to said device is created through said via the hole extending through the substrate and contact with said layer.

10. (Currently amended) The semiconductor device according to claim 9, wherein said single-crystal substrate is one of a comprises a material selected from a group consisting of sapphire substrate, spinel substrate, perovskite yttrium aluminate, substrate and SiC substrate.

11. (Currently amended) The semiconductor device according to claim 9 wherein said semiconductor device is comprises a semiconductor laser using nitride III-V compound semiconductors.

12. (Currently amended) The semiconductor device according to claim 9 wherein said semiconductor device is comprises an FET using nitride III-V compound semiconductors.

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13 - 24. (Canceled)

25. (New) A semiconductor device comprising:

a single-crystal substrate made of a material different from nitride III-V compound semiconductors, said substrate extending between a first surface and a second surface opposite said first surface and having a hole extending through the substrate from said first surface to said second surface;

a device formed on one of said first and second surfaces of said single-crystal substrate using III-V compound semiconductors;

a layer disposed on one of said first and second surfaces of said single-crystal substrate and electrically connected to said device;

wherein a surface of the layer is at least as close to the substrate as a surface of the device facing the substrate; and

wherein an electrical connection to said device is created via the hole extending through the substrate and contact with said layer.